## **Electronic Supporting Information**

## Interaction between H<sub>2</sub>O, N<sub>2</sub>, CO, NO, NO<sub>2</sub> and N<sub>2</sub>O molecules and the defective

## WSe<sub>2</sub> monolayer

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**Table S1.** The nearest atomic distance (d in Å) between the adsorbed molecule and the V<sub>Se</sub> surface for the physisorption state. From the reference (*Dalton Transactions, 2008 (21): 2832-2838*), the sum of the covalent radii of C, N, or O and W (Se) atoms is about 2.3 (1.9) Å, and that of H and W (Se) atoms is about 1.9 (1.5) Å.

molecule	H <sub>2</sub> O	$N_2$	СО	NO	NO <sub>2</sub>	$N_2O$
d	3.17	3.95	3.71	3.36	3.35	3.50



**Fig. S1.** The top and side views of the pristine WSe<sub>2</sub> monolayer with the physisorbed  $H_2O$  (a) and  $N_2$  (b) molecules. The adsorption energy, the number the transferred electrons, and the height of the adsorbed molecule with respect to the upper Se atomic plane are given. The isosurfaces for the CDD are  $2 \times 10^{-4}$  and  $1 \times 10^{-4}$  *e* bohr<sup>-3</sup>, respectively, for the adsorption of the H<sub>2</sub>O and N<sub>2</sub> molecules. The red and green regions represent the electron accumulation and depletion, respectively.



**Fig. S2.** (a) A NO molecule is put above the NO molecule doped WSe<sub>2</sub> monolayer. (b) After structural optimization for the configuration in (a), the NO molecule can combine with the exposed O atom to form a N-doped WSe<sub>2</sub> monolayer with an adsorbed NO<sub>2</sub> molecule.



Fig. S3. The top and side views of the  $N_2O$  molecule adsorption on  $V_{Se}$  with the N atom occupying the Se vacancy site. The adsorption energy for this configuration is 2.40 eV.



Fig. S4. The spin-polarized TDOS of the free CO (a) and NO molecules (b). The  $2\pi^*$  levels near the E<sub>f</sub> are marked.



**Fig. S5.** The LDOS projected on the adsorbed CO for the MC state. The insets show the partial charge densities for the electronic states within -0.2 to 0.0 eV (in 0.003  $e/bohr^3$ ), within 0.7 to 1.0 eV (in 0.003  $e/bohr^3$ ), and within 1.4 to 4.0 eV (in 0.03  $e/bohr^3$ ). The vertical line denotes the Fermi level.



**Fig. S6.** The LDOS projected on the adsorbed NO for the MC state. The insets show the partial charge densities for the electronic states within -0.4 to 0.0 eV (in 0.006  $e/bohr^3$ ), within 0 to 0.2 eV (in 0.003  $e/bohr^3$ ), and within 2.0 to 4.0 eV (in 0.03  $e/bohr^3$ ). The vertical line denotes the Fermi level. The black and red lines indicate the spin-up and spin-down states, respectively.